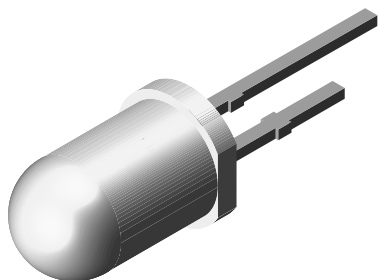




## High Speed Infrared Emitting Diode, 870 nm, GaAlAs Double Hetero



### DESCRIPTION

TSFF5410 is an infrared, 870 nm emitting diode in GaAlAs double hetero (DH) technology with high radiant power and high speed, molded in a clear, untinted plastic package.

### FEATURES

- Package type: leaded
- Package form: T-1 $\frac{3}{4}$
- Dimensions (in mm):  $\varnothing$  5
- Leads with stand-off
- Peak wavelength:  $\lambda_p = 870$  nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity:  $\phi = \pm 22^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- High modulation bandwidth:  $f_c = 24$  MHz
- Good spectral matching to Si photodetectors
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
**GREEN**  
(5-2008)

### APPLICATIONS

- Infrared video data transmission between camcorder and TV set
- Free air data transmission systems with high modulation frequencies or high data transmission rate requirements

### PRODUCT SUMMARY

| COMPONENT | $I_e$ (mW/sr) | $\phi$ (°) | $\lambda_p$ (nm) | $t_r$ (ns) |
|-----------|---------------|------------|------------------|------------|
| TSFF5410  | 70            | $\pm 22$   | 870              | 15         |

#### Note

- Test conditions see table "Basic Characteristics"

### ORDERING INFORMATION

| ORDERING CODE | PACKAGING | REMARKS                      | PACKAGE FORM      |
|---------------|-----------|------------------------------|-------------------|
| TSFF5410      | Bulk      | MOQ: 4000 pcs, 4000 pcs/bulk | T-1 $\frac{3}{4}$ |

#### Note

- MOQ: minimum order quantity

### ABSOLUTE MAXIMUM RATINGS ( $T_{amb} = 25^\circ\text{C}$ , unless otherwise specified)

| PARAMETER                              | TEST CONDITION                          | SYMBOL     | VALUE       | UNIT             |
|----------------------------------------|-----------------------------------------|------------|-------------|------------------|
| Reverse voltage                        |                                         | $V_R$      | 5           | V                |
| Forward current                        |                                         | $I_F$      | 100         | mA               |
| Peak forward current                   | $t_p/T = 0.5$ , $t_p = 100 \mu\text{s}$ | $I_{FM}$   | 200         | mA               |
| Surge forward current                  | $t_p = 100 \mu\text{s}$                 | $I_{FSM}$  | 1           | A                |
| Power dissipation                      |                                         | $P_V$      | 180         | mW               |
| Junction temperature                   |                                         | $T_j$      | 100         | $^\circ\text{C}$ |
| Operating temperature range            |                                         | $T_{amb}$  | -40 to +85  | $^\circ\text{C}$ |
| Storage temperature range              |                                         | $T_{stg}$  | -40 to +100 | $^\circ\text{C}$ |
| Soldering temperature                  | $t \leq 5$ s, 2 mm from case            | $T_{sd}$   | 260         | $^\circ\text{C}$ |
| Thermal resistance junction to ambient | J-STD-051, leads 7 mm, soldered on PCB  | $R_{thJA}$ | 230         | K/W              |

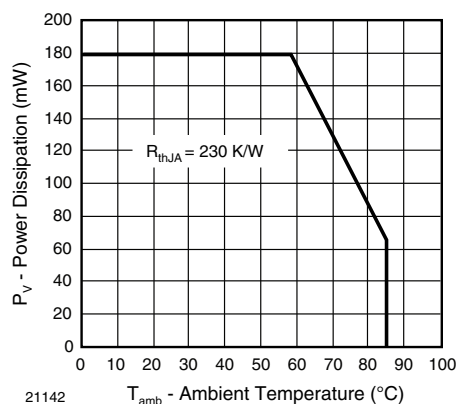


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

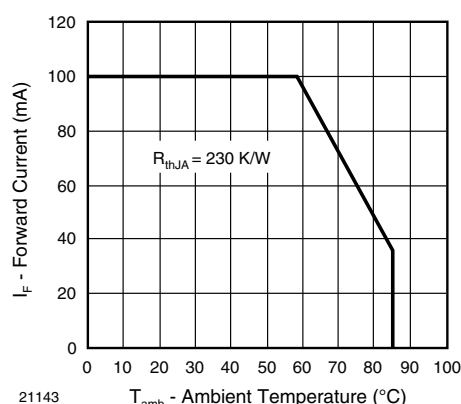


Fig. 2 - Forward Current Limit vs. Ambient Temperature

| BASIC CHARACTERISTICS ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified) |                                                      |                  |      |          |      |               |
|----------------------------------------------------------------------------------------------|------------------------------------------------------|------------------|------|----------|------|---------------|
| PARAMETER                                                                                    | TEST CONDITION                                       | SYMBOL           | MIN. | TYP.     | MAX. | UNIT          |
| Forward voltage                                                                              | $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$         | $V_F$            | -    | 1.5      | 1.8  | V             |
|                                                                                              | $I_F = 1\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$  | $V_F$            | -    | 2.3      | 3    | V             |
| Temperature coefficient of $V_F$                                                             | $I_F = 1\text{ mA}$                                  | $TK_{VF}$        | -    | -1.8     | -    | mV/K          |
| Reverse current                                                                              | $V_R = 5\text{ V}$                                   | $I_R$            | -    | -        | 10   | $\mu\text{A}$ |
| Junction capacitance                                                                         | $V_R = 0\text{ V}$ , $f = 1\text{ MHz}$ , $E = 0$    | $C_j$            | -    | 125      | -    | pF            |
| Radiant intensity                                                                            | $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$         | $I_e$            | 45   | 70       | 135  | mW/sr         |
|                                                                                              | $I_F = 1\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$  | $I_e$            | -    | 700      | -    | mW/sr         |
| Radiant power                                                                                | $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$         | $\phi_e$         | -    | 50       | -    | mW            |
| Temperature coefficient of $\phi_e$                                                          | $I_F = 100\text{ mA}$                                | $TK_{\phi_e}$    | -    | -0.35    | -    | %/K           |
| Angle of half intensity                                                                      |                                                      | $\phi$           | -    | $\pm 22$ | -    | $^{\circ}$    |
| Peak wavelength                                                                              | $I_F = 100\text{ mA}$                                | $\lambda_p$      | -    | 870      | -    | nm            |
| Spectral bandwidth                                                                           | $I_F = 100\text{ mA}$                                | $\Delta\lambda$  | -    | 40       | -    | nm            |
| Temperature coefficient of $\lambda_p$                                                       | $I_F = 100\text{ mA}$                                | $TK_{\lambda_p}$ | -    | 0.25     | -    | nm/K          |
| Rise time                                                                                    | $I_F = 100\text{ mA}$                                | $t_r$            | -    | 15       | -    | ns            |
| Fall time                                                                                    | $I_F = 100\text{ mA}$                                | $t_f$            | -    | 15       | -    | ns            |
| Cut-off frequency                                                                            | $I_{DC} = 70\text{ mA}$ , $I_{AC} = 30\text{ mA pp}$ | $f_c$            | -    | 24       | -    | MHz           |
| Virtual source diameter                                                                      |                                                      | $d$              | -    | 2.1      | -    | mm            |

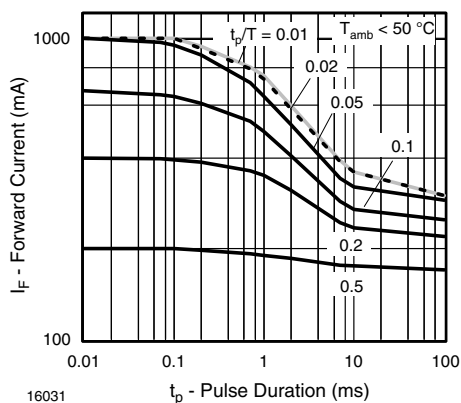
**BASIC CHARACTERISTICS** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)

Fig. 3 - Pulse Forward Current vs. Pulse Duration

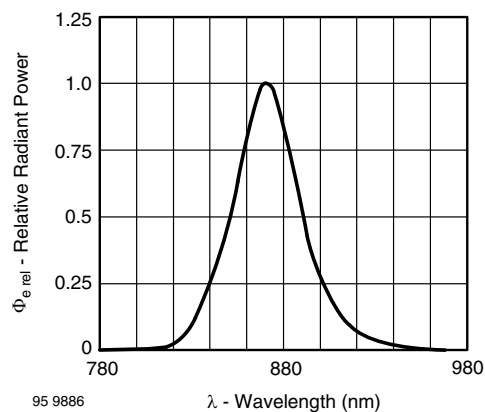


Fig. 6 - Relative Radiant Power vs. Wavelength

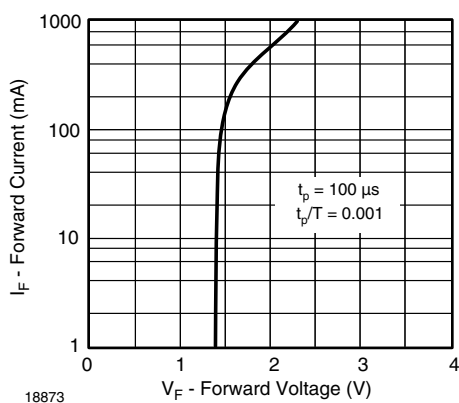


Fig. 4 - Forward Current vs. Forward Voltage

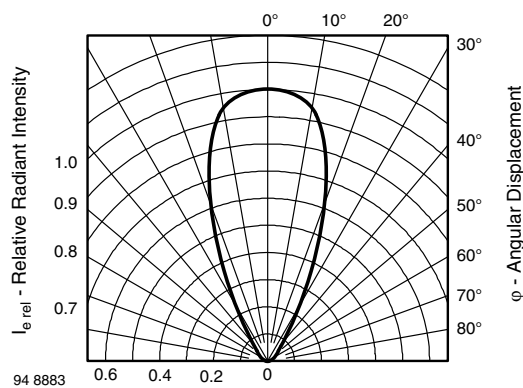


Fig. 7 - Relative Radiant Intensity vs. Angular Displacement

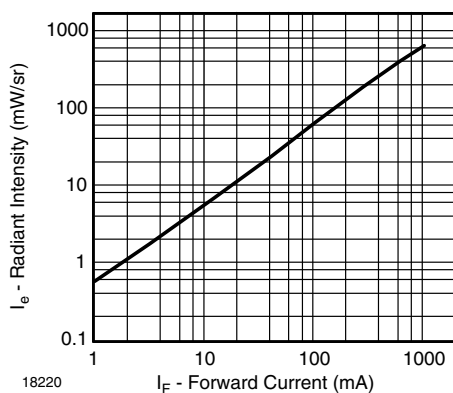


Fig. 5 - Radiant Intensity vs. Forward Current

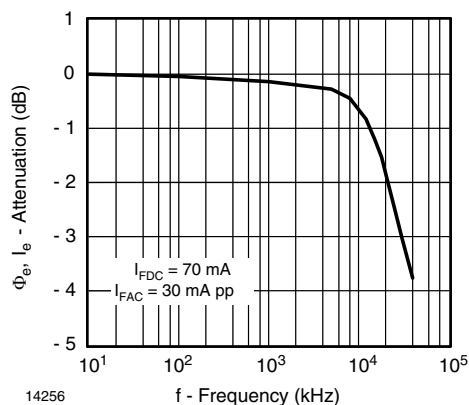
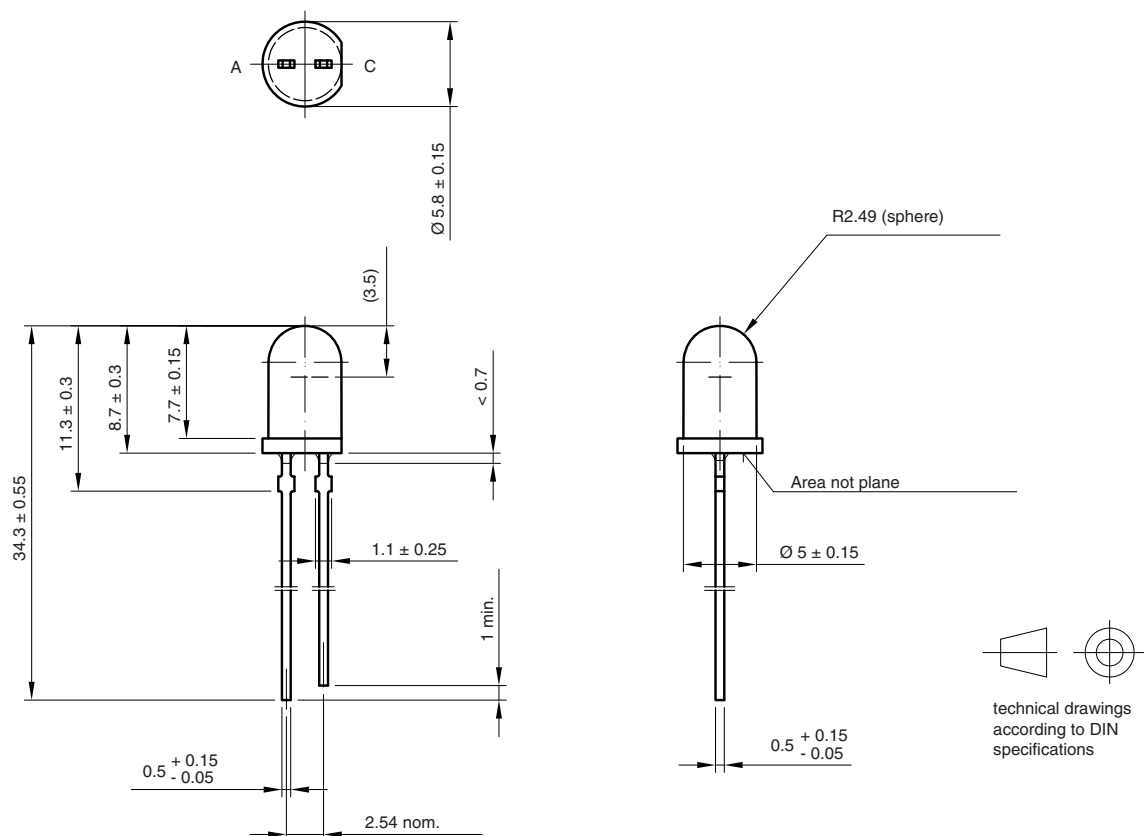


Fig. 8 - Attenuation vs. Frequency

**PACKAGE DIMENSIONS** in millimeters

6.544-5258.06-4  
Issue: 3; 19.05.09  
95 11260



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